



Europäisches Patentamt
European Patent Office
Office européen des brevets



(11) **EP 1 424 735 A8**

(12) **CORRECTED EUROPEAN PATENT APPLICATION**

published in accordance with Art. 158(3) EPC

Note: Bibliography reflects the latest situation

(15) Correction information:
Corrected version no 1 (W1 A1)
INID code(s) 54

(51) Int Cl.7: **H01L 31/042**

(86) International application number:
PCT/JP2002/005730

(48) Corrigendum issued on:
13.04.2005 Bulletin 2005/15

(87) International publication number:
WO 2003/005456 (16.01.2003 Gazette 2003/03)

(43) Date of publication:
02.06.2004 Bulletin 2004/23

(21) Application number: **02733434.1**

(22) Date of filing: **10.06.2002**

(84) Designated Contracting States:
AT BE DE SE

(30) Priority: **06.07.2001 JP 2001244973**
10.10.2001 JP 2001348084

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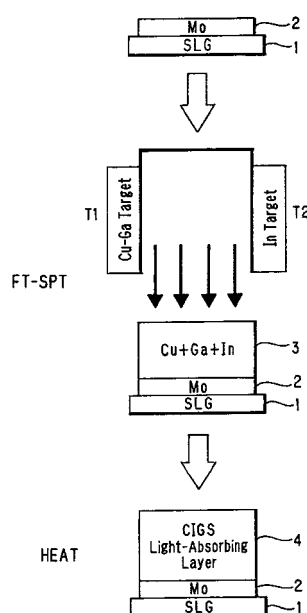
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(54) **METHOD FOR FORMING LIGHT-ABSORBING LAYER**

(57) A method of forming a light-absorbing layer of CIGS for a solar cell by forming a precursor of Ib-IIIb group metals by sputtering and then by treating the precursor in a selenium atmosphere, wherein different kinds of metal element particles are sputtered from a pair of oppositely disposed targets and are well mixed to form a thin-film precursor, and a method of forming a light-absorbing layer for a compound semiconductor solar cell by forming a thin single-layered precursor of an alloy by simultaneously supplying Ib group and IIIb group metal elements and then by exposing the precursor to selenium gas. Both the methods can form a high-quality light-absorbing layer for a compound semiconductor solar cell at a high speed of treatment.

FIG. 3



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